

# MC74HC365A

## Hex 3-State Noninverting Buffer with Common Enables

### High-Performance Silicon-Gate CMOS

The MC74HC365A is identical in pinout to the LS365. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device is a high-speed hex buffer with 3-state outputs and two common active-low Output Enables. When either of the enables is high, the buffer outputs are placed into high-impedance states. The HC365A has noninverting outputs.

#### Features

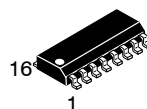
- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0  $\mu$ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 90 FETs or 22.5 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



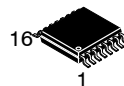
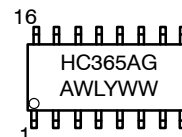
ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

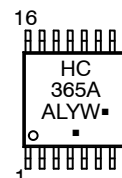
#### MARKING DIAGRAMS



SOIC-16  
D SUFFIX  
CASE 751B



TSSOP-16  
DT SUFFIX  
CASE 948F



A = Assembly Location  
WL, L = Wafer Lot  
YY, Y = Year  
WW, W = Work Week  
G or ■ = Pb-Free Package  
(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# MC74HC365A

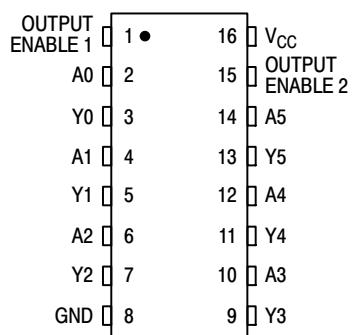


Figure 1. Pin Assignment

FUNCTION TABLE

Inputs			Output
Enable 1	Enable 2	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

X = don't care

Z = high impedance

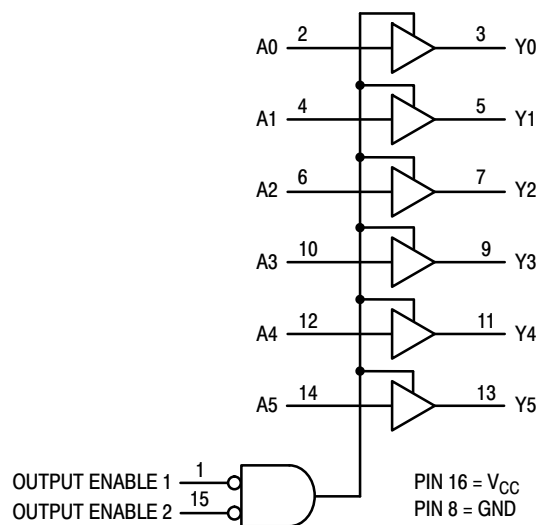


Figure 2. Logic Diagram

## ORDERING INFORMATION

Device	Package	Shipping†
MC74HC365ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC365ADR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
MC74HC365ADTR2G	TSSOP-16 (Pb-Free)	2500 Units / Tape & Reel
NLV74HC365ADTR2G*	TSSOP-16 (Pb-Free)	2500 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

# MC74HC365A

## MAXIMUM RATINGS\*

Symbol	Parameter	Value	Unit
$V_{CC}$	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
$V_{in}$	DC Input Voltage (Referenced to GND)	- 0.5 to $V_{CC} + 0.5$	V
$V_{out}$	DC Output Voltage (Referenced to GND)	- 0.5 to $V_{CC} + 0.5$	V
$I_{in}$	DC Input Current, per Pin	$\pm 20$	mA
$I_{out}$	DC Output Current, per Pin	$\pm 25$	mA
$I_{CC}$	DC Supply Current, $V_{CC}$ and GND Pins	$\pm 50$	mA
$P_D$	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
$T_{stg}$	Storage Temperature	- 65 to + 150	°C
$T_L$	Lead Temperature, 1 mm from Case for 10 Seconds SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating — SOIC Package: - 7 mW/°C from 65° to 125°C  
TSSOP Package: - 6.1 mW/°C from 65° to 125°C

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
$V_{CC}$	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
$V_{in}, V_{out}$	DC Input Voltage, Output Voltage (Referenced to GND)	0	$V_{CC}$	V
$T_A$	Operating Temperature, All Package Types	- 55	+ 125	°C
$t_r, t_f$	Input Rise and Fall Time (Figure 1)	$V_{CC} = 2.0 \text{ V}$ 0 $V_{CC} = 3.0 \text{ V}$ 0 $V_{CC} = 4.5 \text{ V}$ 0 $V_{CC} = 6.0 \text{ V}$ 0	1000 600 500 400	ns

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	$V_{CC}$ V	Guaranteed Limit			Unit
				- 55 to 25°C	$\leq 85^\circ\text{C}$	$\leq 125^\circ\text{C}$	
$V_{IH}$	Minimum High-Level Input Voltage	$V_{out} = V_{CC} - 0.1 \text{ V}$ $ I_{out}  \leq 20 \mu\text{A}$	2.0	1.5	1.5	1.5	V
			3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
$V_{IL}$	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out}  \leq 20 \mu\text{A}$	2.0	0.50	0.50	0.50	V
			3.0	0.90	0.90	0.90	
			4.5	1.35	1.35	1.35	
			6.0	1.80	1.80	1.80	
$V_{OH}$	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out}  \leq 20 \mu\text{A}$	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		$V_{in} = V_{IH}$ $ I_{out}  \leq 3.6 \text{ mA}$ $ I_{out}  \leq 6.0 \text{ mA}$ $ I_{out}  \leq 7.8 \text{ mA}$	3.0	2.48	2.34	2.20	
			4.5	3.98	3.84	3.70	
			6.0	5.48	5.34	5.20	
$V_{OL}$	Maximum Low-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out}  \leq 20 \mu\text{A}$	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		$V_{in} = V_{IL}$ $ I_{out}  \leq 3.6 \text{ mA}$ $ I_{out}  \leq 6.0 \text{ mA}$ $ I_{out}  \leq 7.8 \text{ mA}$	3.0	0.26	0.33	0.40	
			4.5	0.26	0.33	0.40	
			6.0	0.26	0.33	0.40	

# MC74HC365A

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	Guaranteed Limit			Unit
				- 55 to 25°C	≤ 85°C	≤ 125°C	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I <sub>OZ</sub>	Maximum Three-State Leakage Current	Output in High-Impedance State V <sub>in</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>out</sub> = V <sub>CC</sub> or GND	6.0	± 0.5	± 5.0	± 10	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	V <sub>in</sub> = V <sub>CC</sub> or GND I <sub>out</sub> = 0 μA	6.0	4	40	160	μA

## AC ELECTRICAL CHARACTERISTICS (C<sub>L</sub> = 50 pF, Input t<sub>r</sub> = t<sub>f</sub> = 6 ns)

Symbol	Parameter	V <sub>CC</sub> V	Guaranteed Limit			Unit
			- 55 to 25°C	≤ 85°C	≤ 125°C	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	2.0	120	150	180	ns
		3.0	60	75	90	
		4.5	24	30	36	
		6.0	20	26	31	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	2.0	220	275	330	ns
		3.0	110	140	170	
		4.5	44	55	66	
		6.0	37	47	56	
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	2.0	220	275	330	ns
		3.0	110	140	170	
		4.5	44	55	66	
		6.0	37	47	56	
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0	60	75	90	ns
		3.0	22	28	34	
		4.5	12	15	18	
		6.0	10	13	15	
C <sub>in</sub>	Maximum Input Capacitance	—	10	10	10	pF
C <sub>out</sub>	Maximum Three-State Output Capacitance (Output in High-Impedance State)	—	15	15	15	pF
C <sub>PD</sub>	Power Dissipation Capacitance (Per Buffer)*	Typical @ 25°C, V <sub>CC</sub> = 5.0 V			pF	
		60				

\* Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

## SWITCHING WAVEFORMS

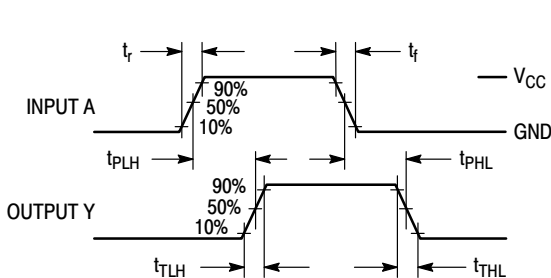


Figure 1.

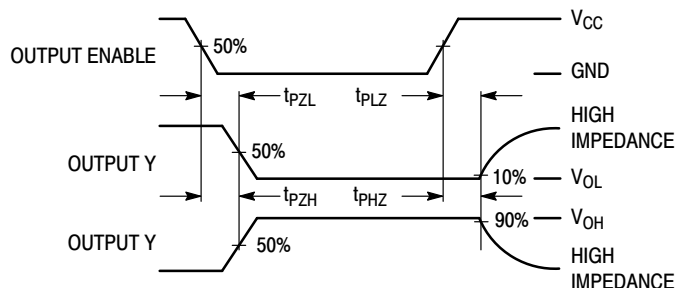
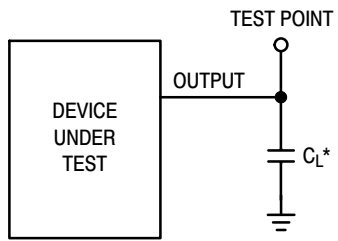


Figure 2.

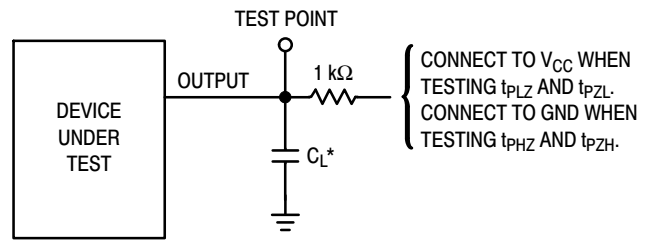
# MC74HC365A

## TEST CIRCUITS



\*Includes all probe and jig capacitance

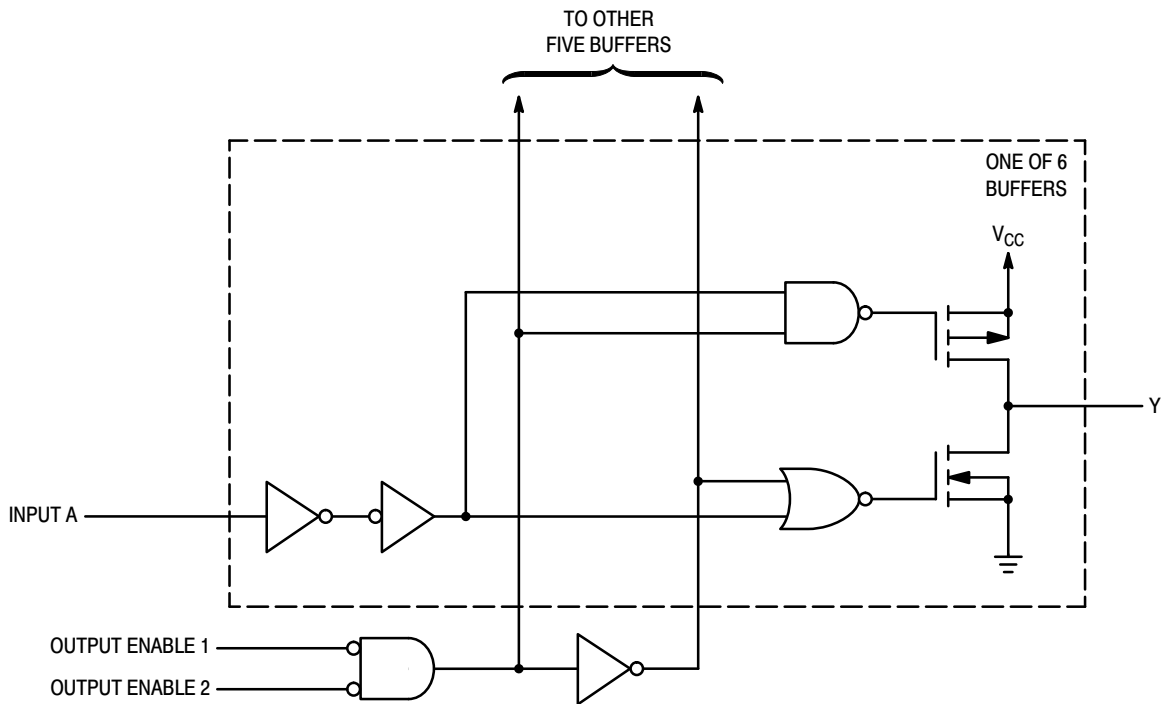
Figure 3.



\*Includes all probe and jig capacitance

Figure 4.

## LOGIC DETAIL



# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1

## SOIC-16 CASE 751B-05 ISSUE K

DATE 29 DEC 2006



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

- |  |  |  |  |
|--|--|--|--|
| <p>STYLE 1:</p> <p>PIN 1. COLLECTOR</p> <p>2. BASE</p> <p>3. EMITTER</p> <p>4. NO CONNECTION</p> <p>5. EMITTER</p> <p>6. BASE</p> <p>7. COLLECTOR</p> <p>8. COLLECTOR</p> <p>9. BASE</p> <p>10. EMITTER</p> <p>11. NO CONNECTION</p> <p>12. EMITTER</p> <p>13. BASE</p> <p>14. COLLECTOR</p> <p>15. EMITTER</p> <p>16. COLLECTOR</p>                           | <p>STYLE 2:</p> <p>PIN 1. CATHODE</p> <p>2. ANODE</p> <p>3. NO CONNECTION</p> <p>4. CATHODE</p> <p>5. CATHODE</p> <p>6. NO CONNECTION</p> <p>7. ANODE</p> <p>8. CATHODE</p> <p>9. CATHODE</p> <p>10. ANODE</p> <p>11. NO CONNECTION</p> <p>12. CATHODE</p> <p>13. CATHODE</p> <p>14. NO CONNECTION</p> <p>15. ANODE</p> <p>16. CATHODE</p> | <p>STYLE 3:</p> <p>PIN 1. COLLECTOR, DYE #1</p> <p>2. BASE, #1</p> <p>3. EMITTER, #1</p> <p>4. COLLECTOR, #1</p> <p>5. COLLECTOR, #2</p> <p>6. BASE, #2</p> <p>7. EMITTER, #2</p> <p>8. COLLECTOR, #2</p> <p>9. COLLECTOR, #3</p> <p>10. BASE, #3</p> <p>11. EMITTER, #3</p> <p>12. COLLECTOR, #3</p> <p>13. COLLECTOR, #4</p> <p>14. BASE, #4</p> <p>15. EMITTER, #4</p> <p>16. COLLECTOR, #4</p>   | <p>STYLE 4:</p> <p>PIN 1. COLLECTOR, DYE #1</p> <p>2. COLLECTOR, #1</p> <p>3. COLLECTOR, #2</p> <p>4. COLLECTOR, #2</p> <p>5. COLLECTOR, #3</p> <p>6. COLLECTOR, #3</p> <p>7. COLLECTOR, #4</p> <p>8. COLLECTOR, #4</p> <p>9. BASE, #4</p> <p>10. EMITTER, #4</p> <p>11. BASE, #3</p> <p>12. EMITTER, #3</p> <p>13. BASE, #2</p> <p>14. EMITTER, #2</p> <p>15. BASE, #1</p> <p>16. EMITTER, #1</p> |
| <p>STYLE 5:</p> <p>PIN 1. DRAIN, DYE #1</p> <p>2. DRAIN, #1</p> <p>3. DRAIN, #2</p> <p>4. DRAIN, #2</p> <p>5. DRAIN, #3</p> <p>6. DRAIN, #3</p> <p>7. DRAIN, #4</p> <p>8. DRAIN, #4</p> <p>9. GATE, #4</p> <p>10. SOURCE, #4</p> <p>11. GATE, #3</p> <p>12. SOURCE, #3</p> <p>13. GATE, #2</p> <p>14. SOURCE, #2</p> <p>15. GATE, #1</p> <p>16. SOURCE, #1</p> | <p>STYLE 6:</p> <p>PIN 1. CATHODE</p> <p>2. CATHODE</p> <p>3. CATHODE</p> <p>4. CATHODE</p> <p>5. CATHODE</p> <p>6. CATHODE</p> <p>7. CATHODE</p> <p>8. CATHODE</p> <p>9. ANODE</p> <p>10. ANODE</p> <p>11. ANODE</p> <p>12. ANODE</p> <p>13. ANODE</p> <p>14. ANODE</p> <p>15. ANODE</p> <p>16. ANODE</p>                                 | <p>STYLE 7:</p> <p>PIN 1. SOURCE N-CH</p> <p>2. COMMON DRAIN (OUTPUT)</p> <p>3. COMMON DRAIN (OUTPUT)</p> <p>4. GATE P-CH</p> <p>5. COMMON DRAIN (OUTPUT)</p> <p>6. COMMON DRAIN (OUTPUT)</p> <p>7. COMMON DRAIN (OUTPUT)</p> <p>8. SOURCE P-CH</p> <p>9. SOURCE P-CH</p> <p>10. COMMON DRAIN (OUTPUT)</p> <p>11. COMMON DRAIN (OUTPUT)</p> <p>12. COMMON DRAIN (OUTPUT)</p> <p>13. GATE N-CH</p> <p>14. COMMON DRAIN (OUTPUT)</p> <p>15. COMMON DRAIN (OUTPUT)</p> <p>16. SOURCE N-CH</p> |  |

### SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

DOCUMENT NUMBER:	98ASB42566B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOIC-16	PAGE 1 OF 1

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



TSSOP-16  
CASE 948F-01  
ISSUE B

DATE 19 OCT 2006



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM\*



- XXXX = Specific Device Code
- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- G or ■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

DOCUMENT NUMBER:	98ASH70247A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TSSOP-16	PAGE 1 OF 1

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Email Requests to: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**onsemi Website:** [www.onsemi.com](http://www.onsemi.com)

### TECHNICAL SUPPORT

**North American Technical Support:**  
Voice Mail: 1 800-282-9855 Toll Free USA/Canada  
Phone: 011 421 33 790 2910

**Europe, Middle East and Africa Technical Support:**

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative